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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



FK8V03050L

Silicon N-channel MOSFET

For lithium-ion secondary battery protection circuit
 For DC-DC Converter

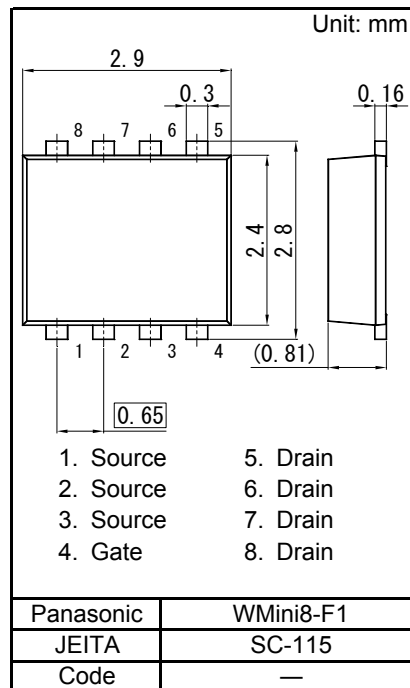
■ Features

- Low drain-source On-state Resistance
 RDS(on) typ = 16 mΩ (VGS = 4.5 V)
- High-speed switching : Qg = 5.1 nC
- Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: 3E

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)



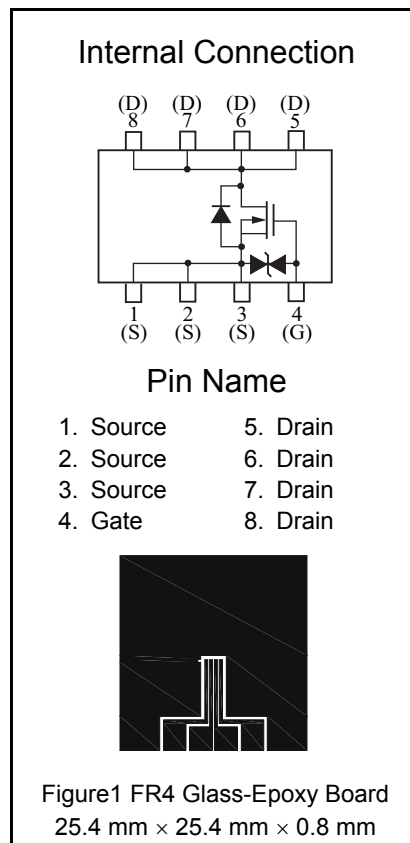
- | | |
|-----------|----------|
| 1. Source | 5. Drain |
| 2. Source | 6. Drain |
| 3. Source | 7. Drain |
| 4. Gate | 8. Drain |

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain-source Voltage	VDS	33	V
Gate-source Voltage	VGS	±20	V
Drain Current (Steady State) *1	ID	8	A
Drain Current (t = 10 s) *1		10	
Drain Current (Pulsed) *1,*2		32	
Source Current (Pulsed) (Body Diode) *1,*2	ISp (BD)	8	
Total Power Dissipation (Steady State) *1	PD	1	W
Total Power Dissipation (t = 10 s) *1		1.5	
Channel Temperature	Tch	150	°C
Operating Ambient Temperature	Topr	-40 to +85	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Note) *1 Device mounted on a glass-epoxy board (See Figure 1)

*2 Pulse test: Ensure that the channel temperature does not exceed 150°C



■ Electrical Characteristics Ta = 25°C ± 3°C

Static Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	33			V
Zero Gate Voltage Drain Current	IDSS	VDS = 33 V, VGS = 0 V			10	μA
Gate-source Leakage Current	IGSS	VGS = ±16 V, VDS = 0 V			±10	μA
Gate-source Threshold Voltage	Vth	ID = 0.73 mA, VDS = 10 V	1		2.5	V
Drain-source On-state Resistance *1	RDS(on)1	ID = 4A, VGS = 10 V		11	15	mΩ
	RDS(on)2	ID = 4A, VGS = 4.5 V		16	25	

Dynamic Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V, f = 1 MHz		520		pF
Output Capacitance	Coss			110		
Reverse Transfer Capacitance	Crss			70		
Turn-on Delay Time *2	td(on)	VDD = 15 V, VGS = 0 to 10 V		8		ns
Rise Time *2	tr	ID = 4 A		4		
Turn-off Delay Time *2	td(off)	VDD = 15 V, VGS = 10 to 0 V		32		
Fall Time *2	tf	ID = 4 A		10		
Total Gate Charge	Qg	VDD = 15 V, VGS = 0 to 4.5 V, ID = 8 A		5.1		nC
Gate-source Charge	Qgs			1.8		
Gate-drain Charge	Qgd			2.3		

Body Diode Characteristic

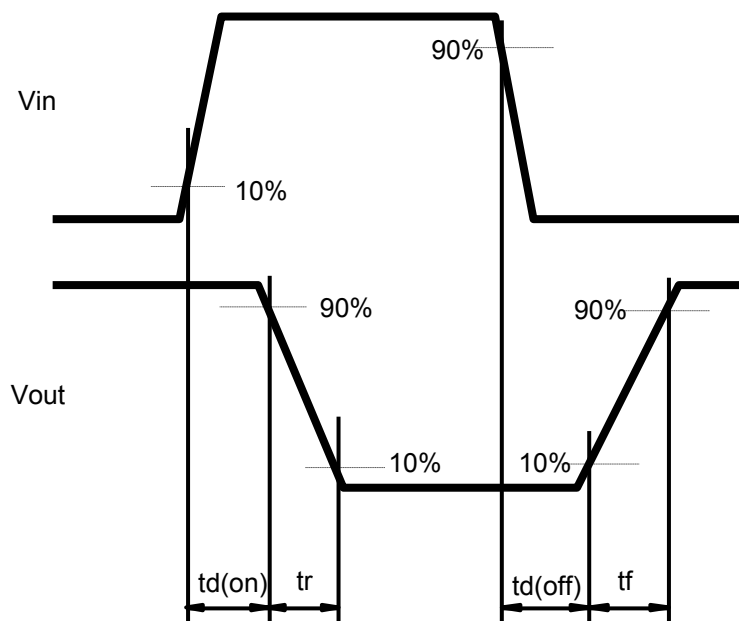
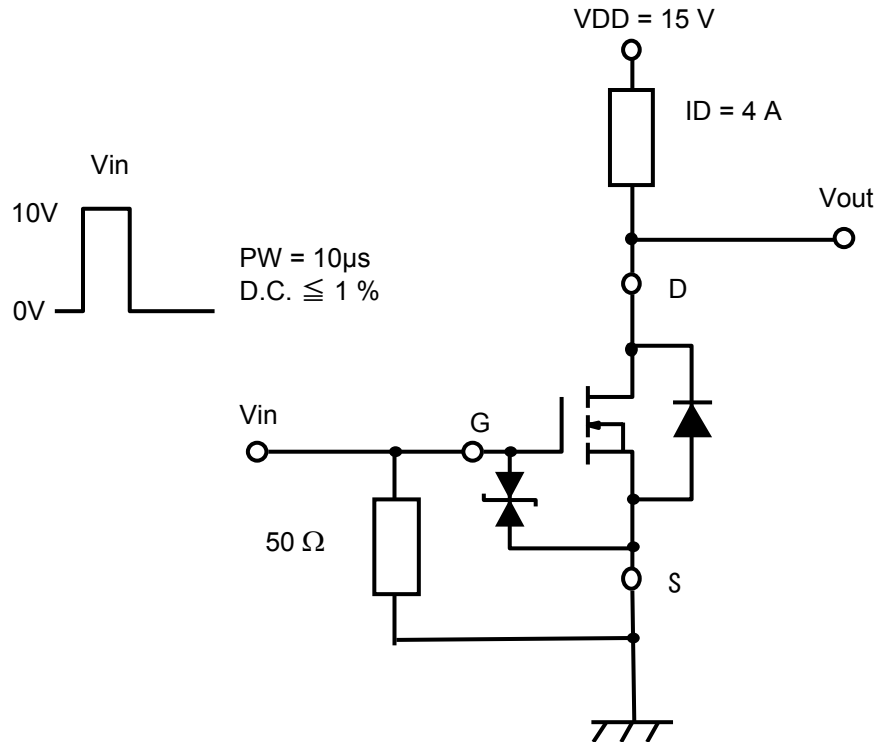
Diode Forward Voltage *1	VSD	IS = 4 A, VGS = 0 V	Min	Typ	Max	Unit
				0.8	1.2	V

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

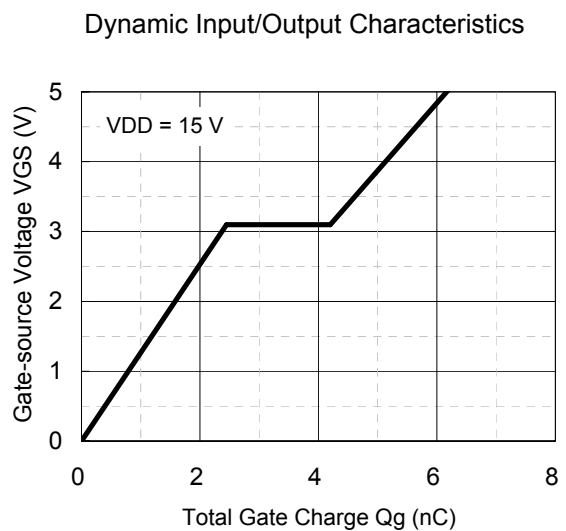
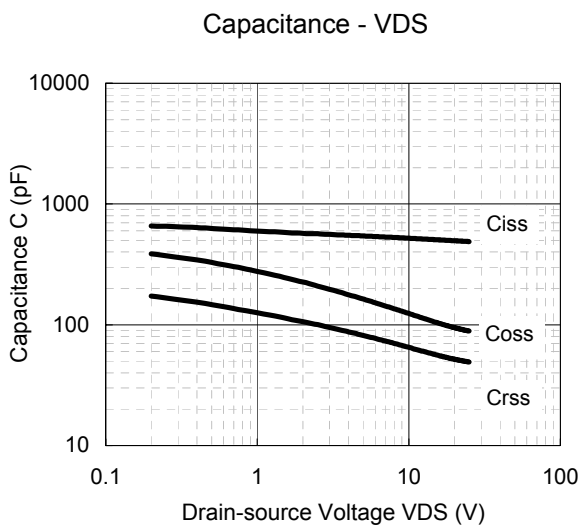
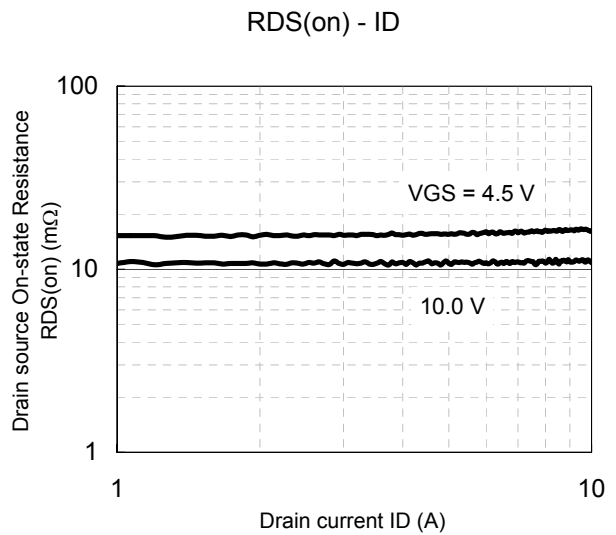
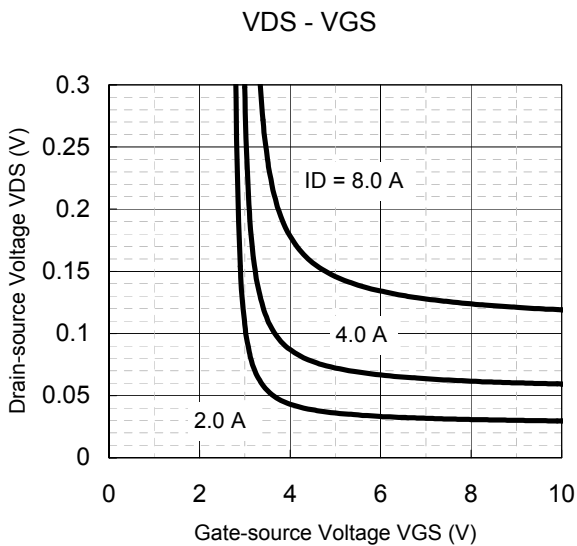
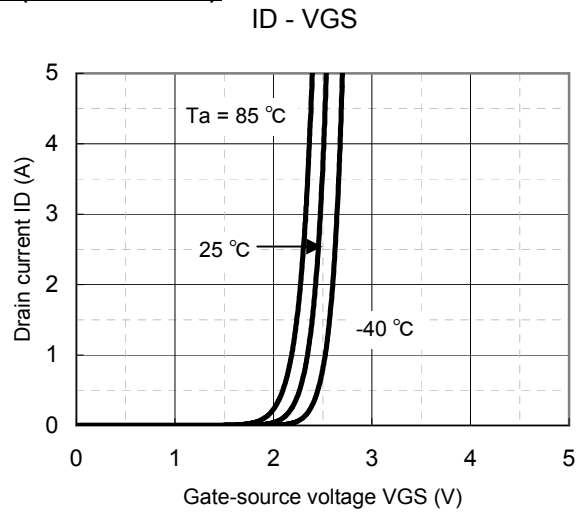
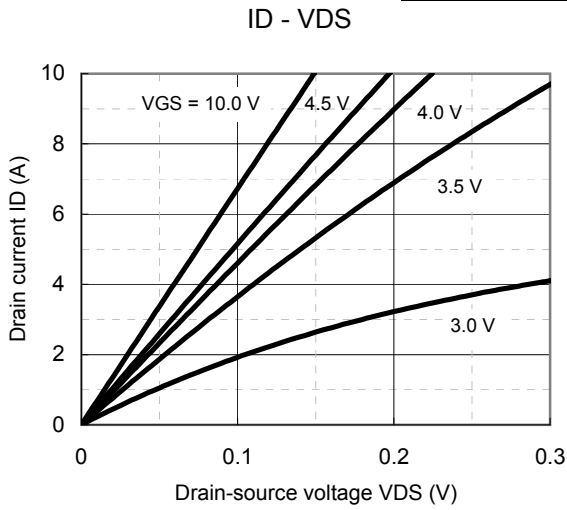
2. *1 Pulse test: Ensure that the channel temperature does not exceed 150°C

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

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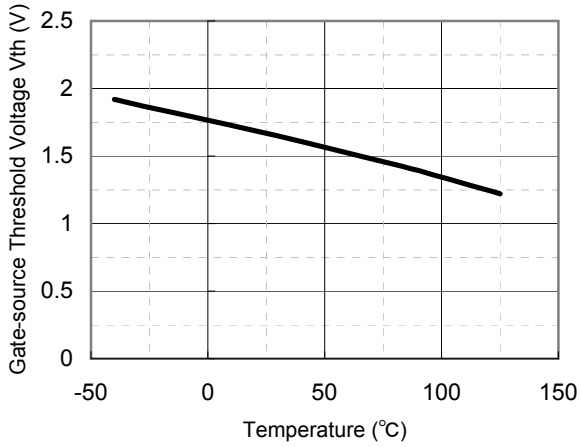


Technical Data (reference)

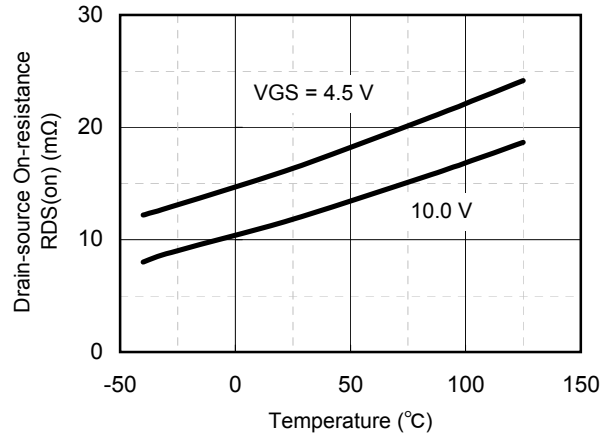


Technical Data (reference)

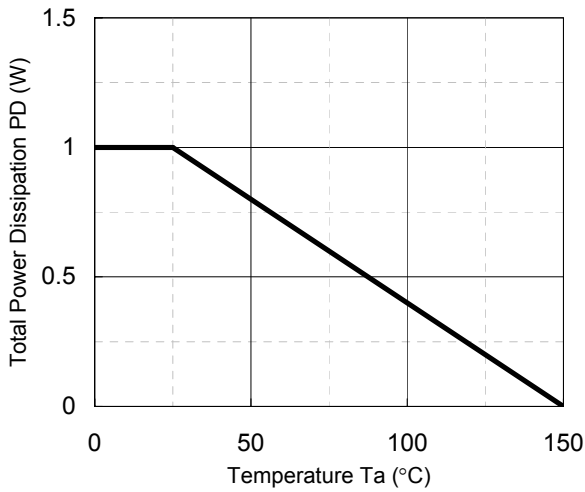
V_{th} - T_a



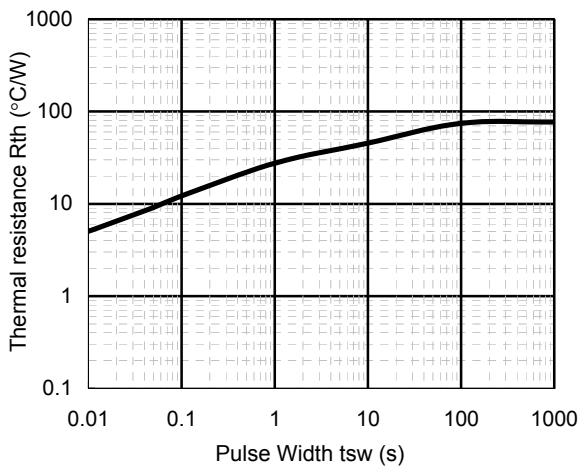
R_{DS(on)} - T_a



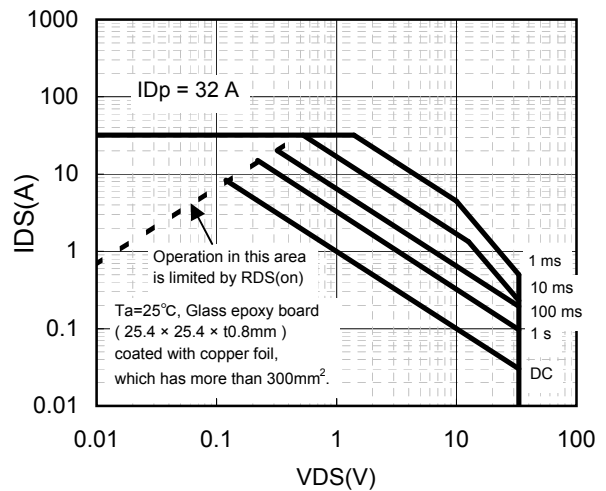
PD - T_a



R_{th} - t_{sw}

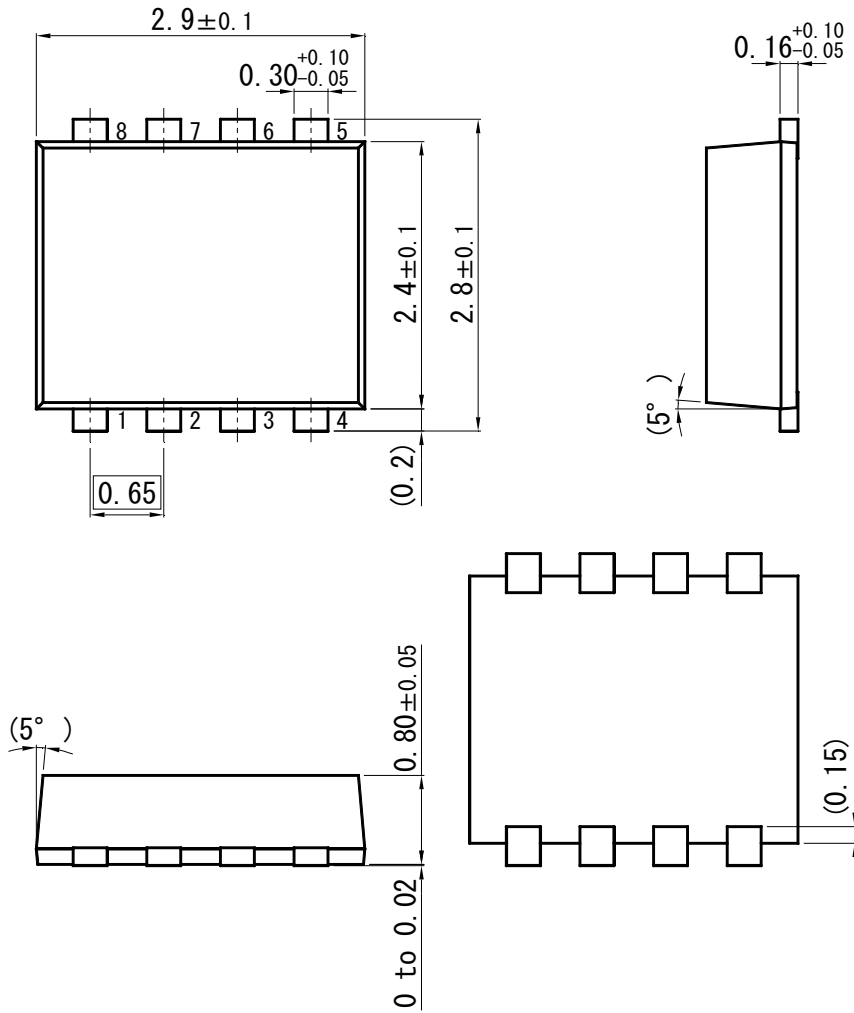


Safe Operating Area

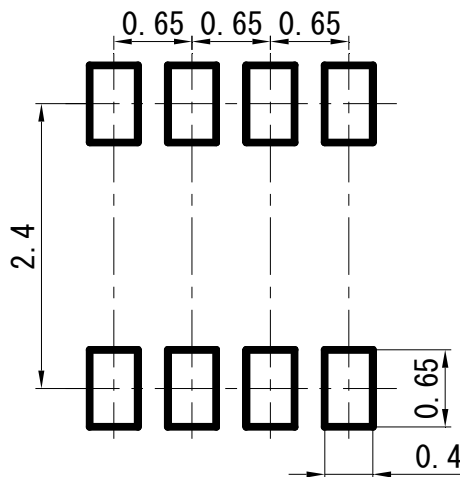


WMini8-F1

Unit : mm



■ Land Pattern (Reference) (Unit : mm)



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